NSN 5962-01-067-8373

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Between 0.750 inches and 0.855 inches

Body Width:

Between 0.200 inches and 0.300 inches

Body Height:

Between 0.150 inches and 0.185 inches

Maximum Power Dissipation Rating:

650.0 milliwatts

Operating Tempurature Range:

+0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs and w/storage and programmable and programmed and w/enable and w/disable and w/open collector and w/decoded output and high speed and w/buffered output

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

6 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

15476-23040a1 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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